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Anmelder/Applicant/Demandeur/Patentinhaber/Proprietor/Titulaire
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COMMUNICATION

The European Patent Office herewith transmits as an enclosure the European search report for the above-mentioned European patent application.

If applicable, copies of the documents cited in the European search report are attached.

Additional set(s) of copies of the documents cited in the European search report is (are) enclosed as well.

The following specifications given by the applicant have been approved by the Search Division:

□ abstract

TX title

The abstract was modified by the Search Division and the definitive text is attached to this communication.

The following figure will be published together with the abstract:

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REFUND OF THE SEARCH FEE

If applicable under Article 10 Rules relating to fees, a separate communication from the Receiving Section on the refund of the search fee will be sent later.



ANNEX TO THE EUROPEAN SEARCH REPORT ON EUROPEAN PATENT APPLICATION NO.

EP 03 01 4110

This annex lists the patent family members relating to the pat int documents cited in the above-mentioned European search report. The members are as contained in the European Patent Office EDP file on The European Patent Office is in no way liable for these particulars which are merely given for the purpose of information.

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ABSTRACT / ZUSAMMENFASSUNG / ABREGE

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A high-frequency switch (10) comprises: a substrate (11); a main line electrode (12) provided between two terminals; a stub line electrode (15) with one end thereof connected to the side edge of the main line electrode and the other end thereof grounded; and a ground electrode (16) provided adjacent to the stub line electrode in the width direction thereof; wherein the substrate has a semiconductor activation layer (19) which extends to below the stub line electrode (15) and the ground electrode (16) between at least one side edge of the stubline electrode and the ground electrode; and wherein a gate electrode (20) which extends in the longitudinal direction of the stub line electrode is provided on the semiconductor activation layer between the stub line electrode and the ground electrode, thereby forming an FET structure, thus providing a high-frequency switch and electronic device therewith, capable of using high frequencies, having reduced insertion loss, and high signal cutoff capabilities.